

## **Description**

The PNMT20V3 uses advanced trench technology

to provide excellent RDS(ON), low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

### **General Features**

 $V_{DS} = 20V I_{D} = 3.0 A$ 

 $R_{DS(ON)} < 53 \text{m}\Omega$ @  $V_{GS}=4.5V$ 

## **Application**

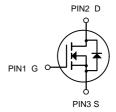
Battery protection

Load switch

Uninterruptible power supply



SOT-23



N-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
PNMT20V3	SOT-23	2300 XXXX	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	20	V
Vgs	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current-Continuous	3.0	А
l	Drain Current-Pulsed (Note 1)	16	А
P <sub>D</sub>	Maximum Power Dissipation	0.9	W
TJ,Tsтg	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	139	°C/W



## Electrical Characteristics (T<sub>A</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	22	-	V
Zero Gate Voltage Drain Current	loss	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.5	0.75	1.2	٧
	_	V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.0A	-	48	60	mΩ
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.8A	-	43	53	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =2.8A	-	8	-	S
Input Capacitance	Clss		-	260	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,	-	48	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	27	-	PF
Turn-on Delay Time	td(on)		-	2.5	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =10V, R <sub>L</sub> =3.3Ω	-	3.2	-	nS
Turn-Off Delay Time	td(off)	$V_{GS}$ =4.5 $V$ , $R_{GEN}$ =6 $\Omega$	-	21	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3	-	nS
Total Gate Charge	Qg		-	2.9	5	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =10V,I <sub>D</sub> =2.8A,	-	0.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =4.5V	-	0.6	-	nC
Diode Forward Voltage (Note 3)	Vsp	V <sub>GS</sub> =0V,I <sub>S</sub> =2.8A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3.3	Α

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**

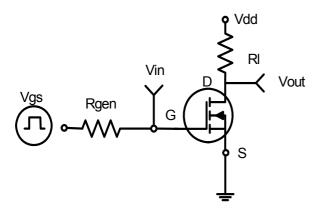


Figure 1:Switching Test Circuit

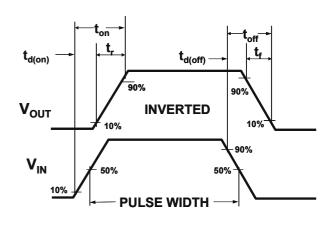
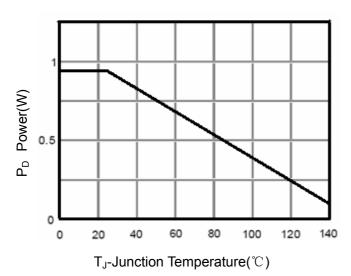
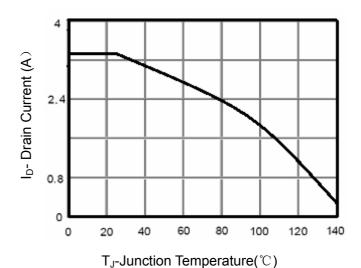


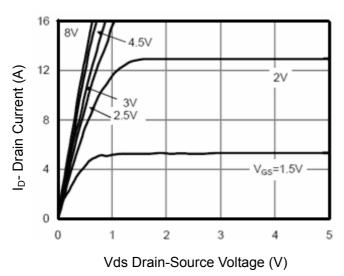
Figure 2:Switching Waveforms



**Figure 3 Power Dissipation** 



**Figure 4 Drain Current** 



**Figure 5 Output Characteristics** 

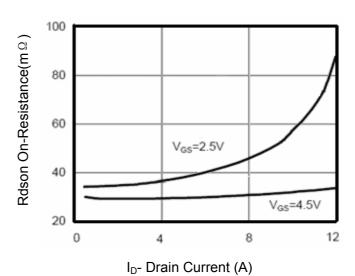
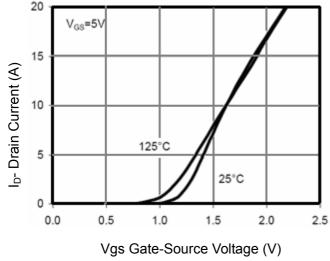
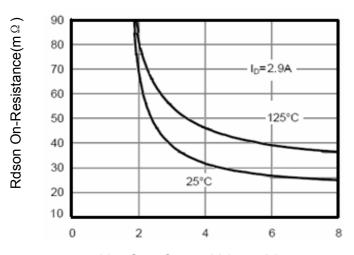


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs

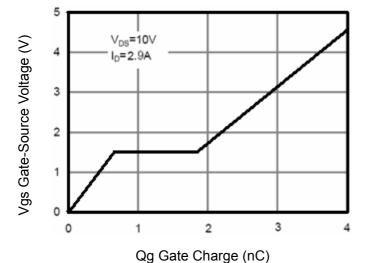


Figure 11 Gate Charge

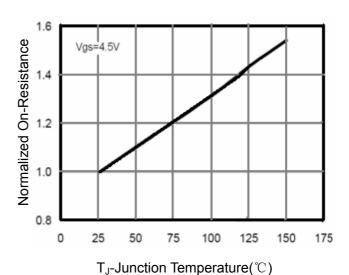
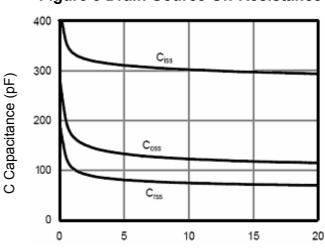
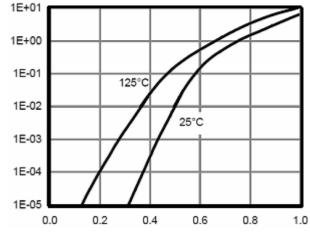


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)





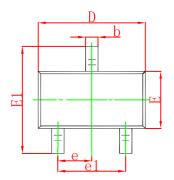
Is- Reverse Drain Current (A)

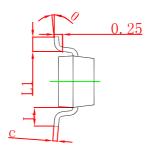
Vsd Source-Drain Voltage (V)

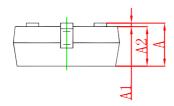
Figure 12 Source- Drain Diode Forward



# **SOT-23 Package Outline Dimensions**

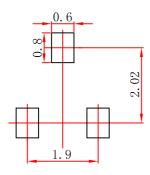






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	0.037 TYP		TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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